

Ordering number : ENN7150

P-Channel Silicon MOSFET



2SJ591LS

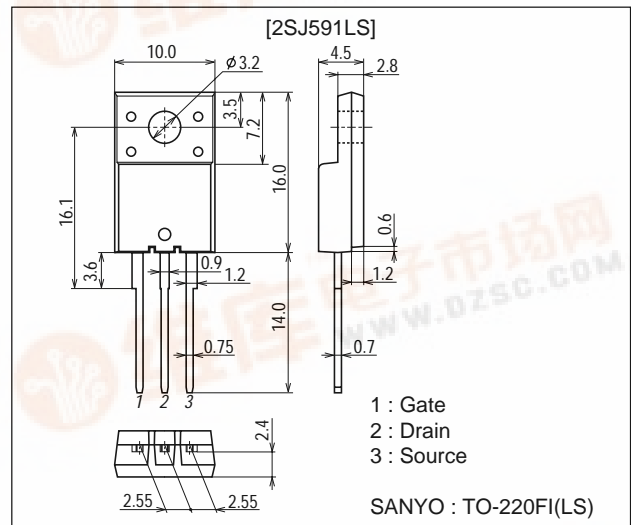
DC / DC Converter Applications

Features

- Low ON-resistance.
- 4V drive.

Package Dimensions

unit : mm
2078C



Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------------|------------------|------------------------|-------------|------|
| Drain-to-Source Voltage | V _{DSS} | | -60 | V |
| Gate-to-Source Voltage | V _{GSS} | | ±20 | V |
| Drain Current (DC) | I _D | | -28 | A |
| Drain Current (Pulse) | I _{DP} | PW≤10μs, duty cycle≤1% | -112 | A |
| Allowable Power Dissipation | P _D | | 2.0 | W |
| | | Tc=25°C | 35 | W |
| Channel Temperature | T _{ch} | | 150 | °C |
| Storage Temperature | T _{stg} | | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--|----------------------|---|---------|-----|------|------|
| | | | min | typ | max | |
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | I _D =-1mA, V _{GS} =0 | -60 | | | V |
| Zero-Gate Voltage Drain Current | I _{DSS} | V _{DS} =-60V, V _{GS} =0 | | | -10 | μA |
| Gate-to-Source Leakage Current | I _{GSS} | V _{GS} =±16V, V _{DS} =0 | | | ±10 | μA |
| Cutoff Voltage | V _{GS(off)} | V _{DS} =-10V, I _D =-1mA | -1.0 | | -2.4 | V |
| Forward Transfer Admittance | y _{fs} | V _{DS} =-10V, I _D =-14A | 18 | 26 | | S |
| Static Drain-to-Source On-State Resistance | R _{DS(on)1} | I _D =-14A, V _{GS} =-10V | | 27 | 35 | mΩ |
| | R _{DS(on)2} | I _D =-14A, V _{GS} =-4V | | 38 | 53 | mΩ |

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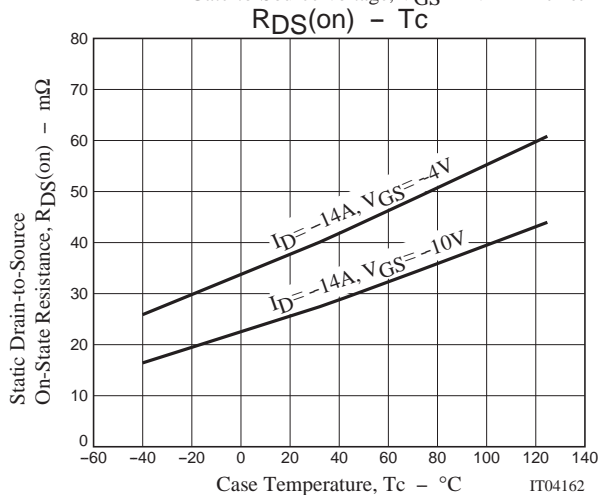
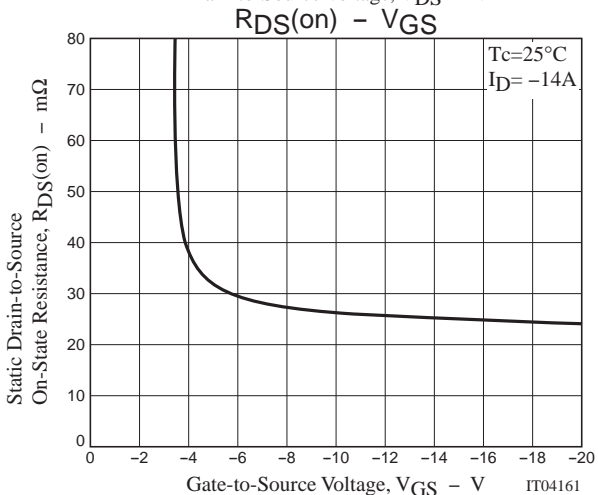
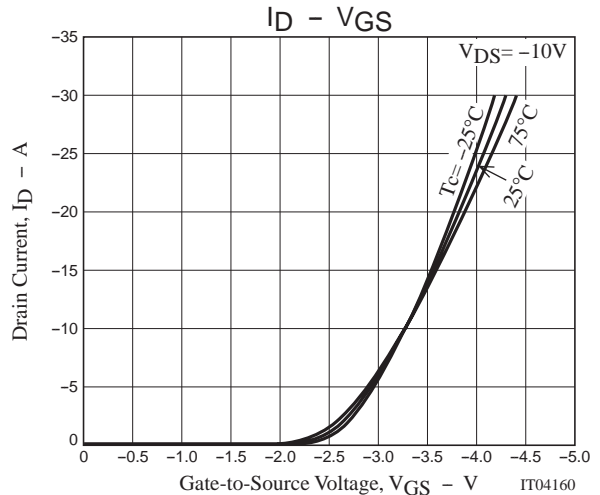
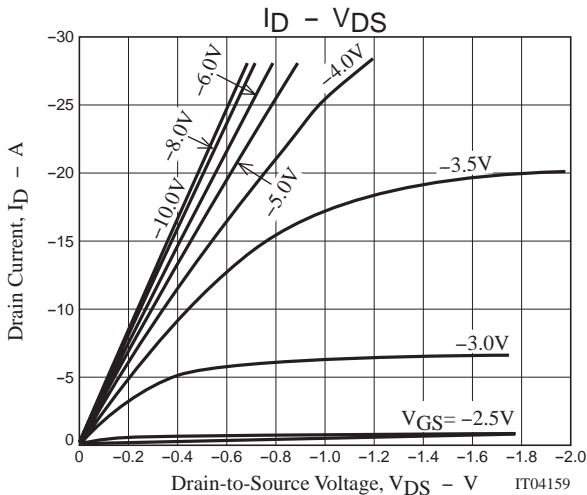
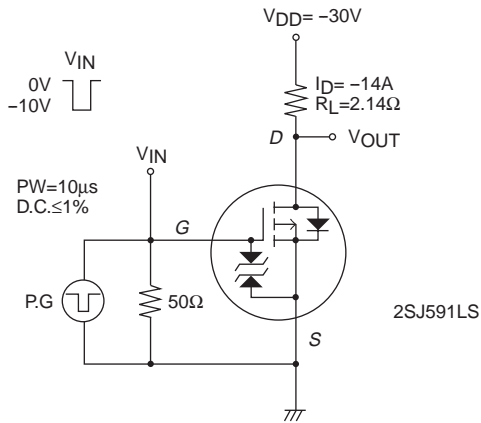


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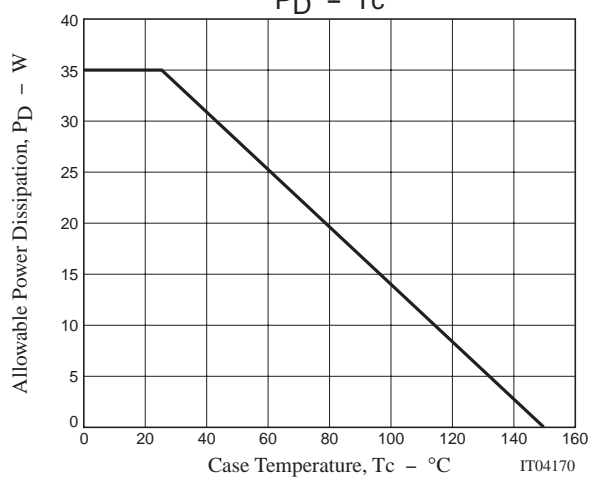
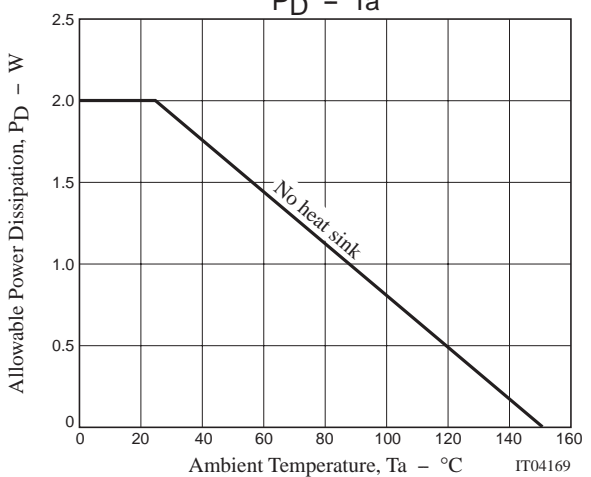
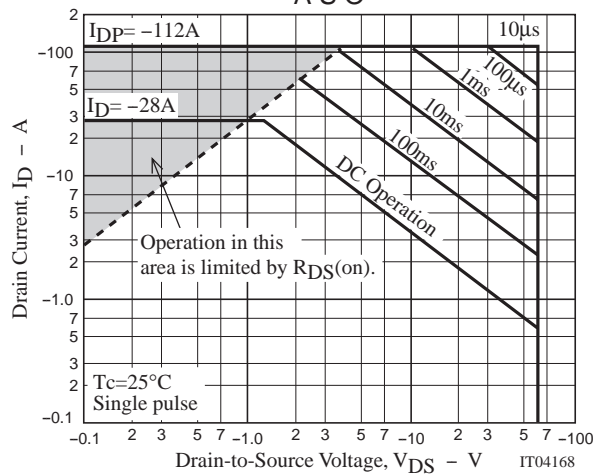
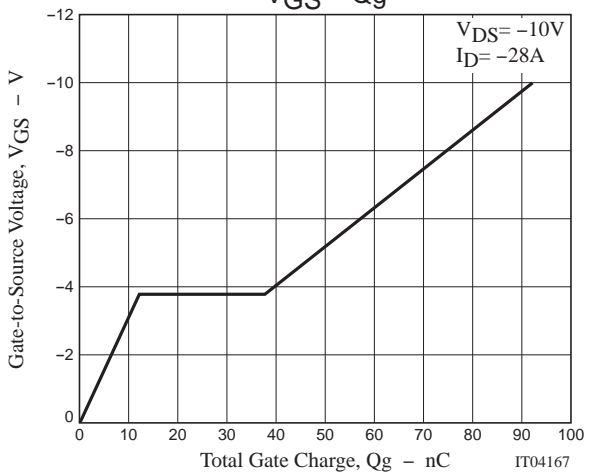
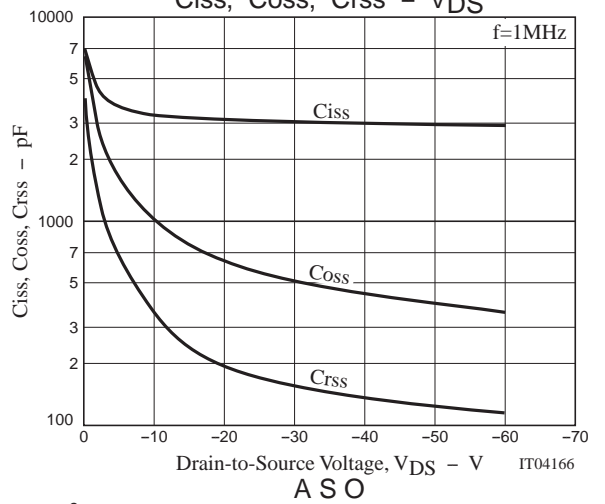
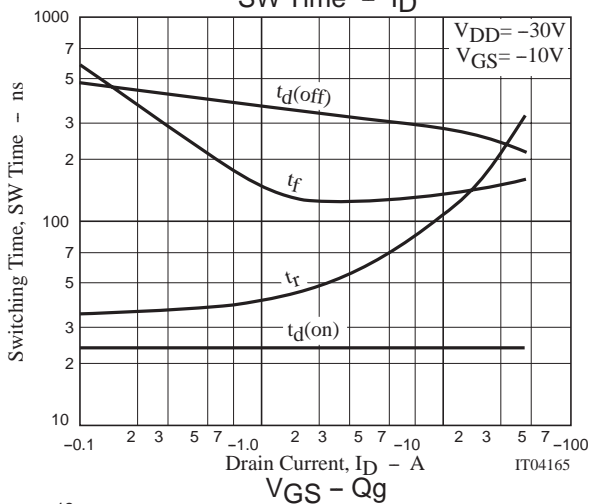
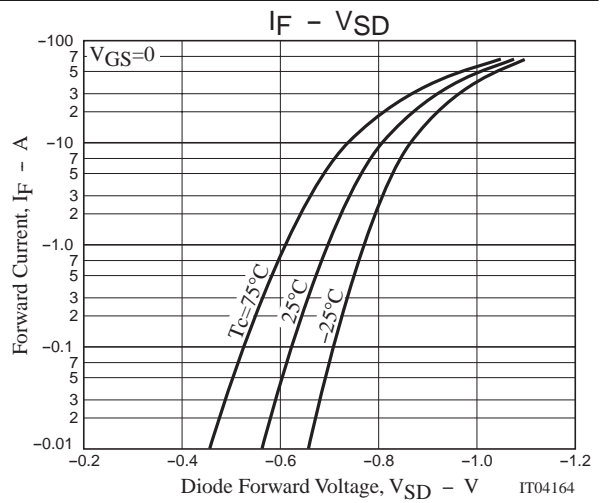
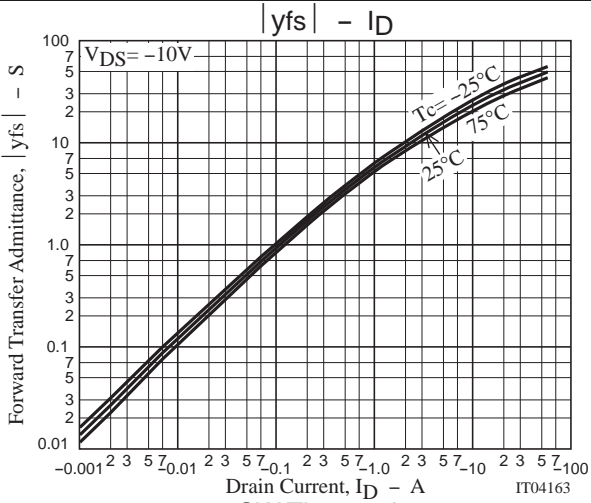
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| Parameter | Symbol | Conditions | Ratings | | | Unit |
|-------------------------------|---------------------|--|---------|------|------|------|
| | | | min | typ | max | |
| Input Capacitance | Ciss | V _{DS} =-20V, f=1MHz | | 3100 | | pF |
| Output Capacitance | Coss | V _{DS} =-20V, f=1MHz | | 640 | | pF |
| Reverse Transfer Capacitance | Crss | V _{DS} =-20V, f=1MHz | | 200 | | pF |
| Turn-ON Delay Time | t _{d(on)} | See specified Test Circuit. | | 24 | | ns |
| Rise Time | t _r | See specified Test Circuit. | | 140 | | ns |
| Turn-OFF Delay Time | t _{d(off)} | See specified Test Circuit. | | 270 | | ns |
| Fall Time | t _f | See specified Test Circuit. | | 140 | | ns |
| Total Gate Charge | Q _g | V _{DS} =-10V, V _{GS} =-10V, I _D =-28A | | 92 | | nC |
| Gate-to-Source Charge | Q _{gs} | V _{DS} =-10V, V _{GS} =-10V, I _D =-28A | | 12 | | nC |
| Gate-to-Drain "Miller" Charge | Q _{gd} | V _{DS} =-10V, V _{GS} =-10V, I _D =-28A | | 26 | | nC |
| Diode Forward Voltage | V _{SD} | I _S =-28A, V _{GS} =0 | -0.92 | | -1.2 | V |

Switching Time Test Circuit



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